



PRODUCT DATA SHEET



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Datasheet



Resources

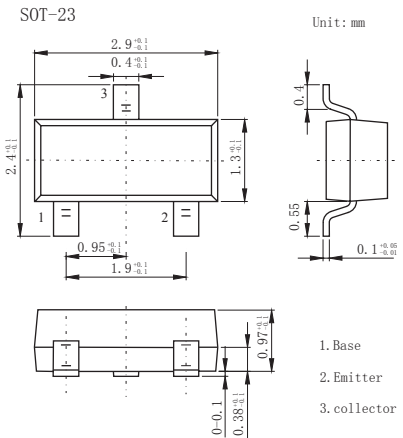


Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.

■ Features

- Low noise and high gain.
 $NF = 1.1 \text{ dB Typ.}, G_a = 11 \text{ dB Typ. @} V_{CE} = 10 \text{ V}, I_c = 7 \text{ mA}, f = 1.0 \text{ GHz}$
- High power gain.
 $MAG = 13 \text{ dB Typ. @} V_{CE} = 10 \text{ V}, I_c = 20 \text{ mA}, f = 1.0 \text{ GHz}$

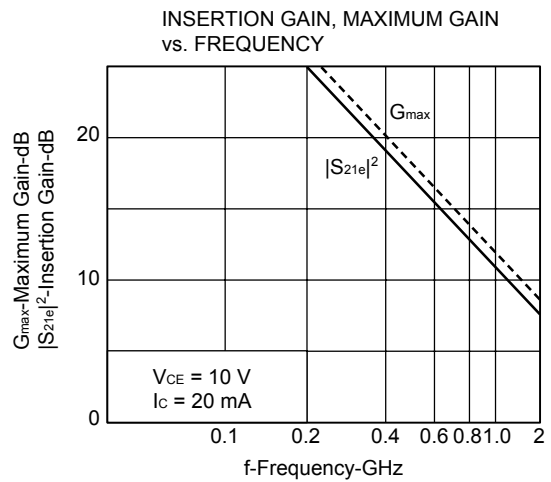
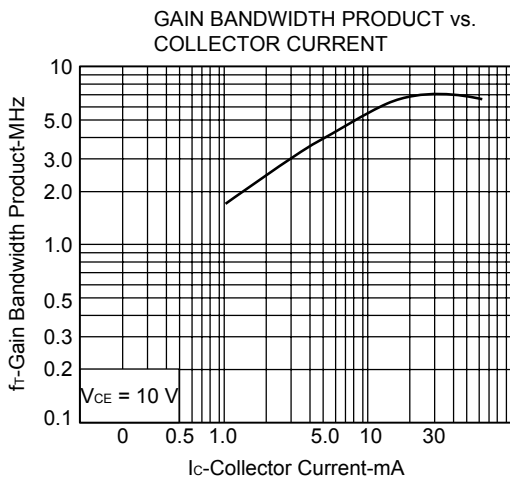
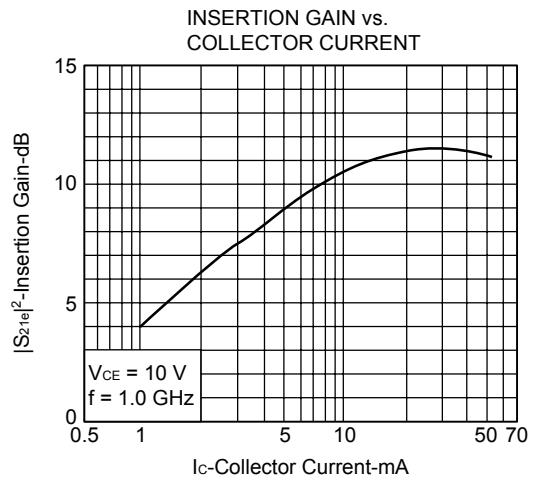
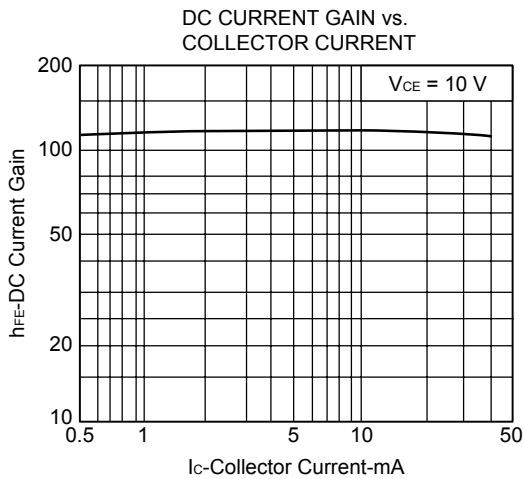
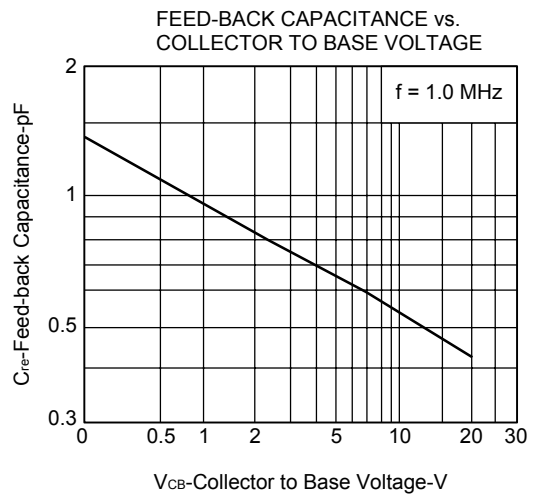
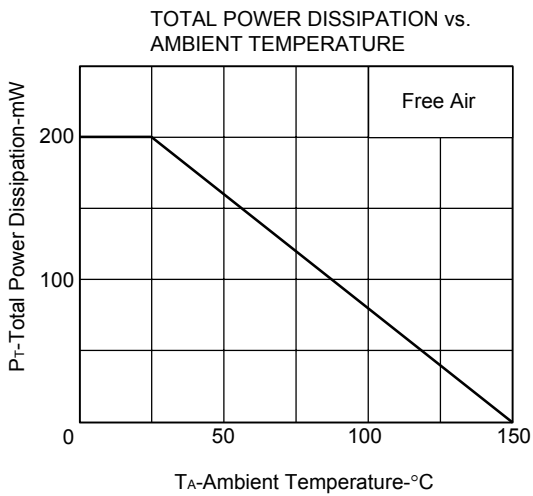

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	20	V
Collector to emitter voltage	V_{CEO}	12	V
Emitter to base voltage	V_{EBO}	3.0	V
Collector current (DC)	I_c	100	mA
Total power dissipation	P_{tot}	200	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-65 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_c = 100 \mu\text{A}, I_E = 0$	20			V
Collector- emitter breakdown voltage	V_{CEO}	$I_c = 1 \text{ mA}, I_B = 0$	12			
Emitter - base breakdown voltage	V_{EBO}	$I_E = 100 \mu\text{A}, I_c = 0$	3			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 10 \text{ V}, I_E = 0$			1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 3 \text{ V}, I_c = 0$			1	
Collector-emitter saturation voltage *	$V_{CE(sat)}$	$I_c = 50 \text{ mA}, I_B = 5 \text{ mA}$			0.4	V
Base - emitter saturation voltage *	$V_{BE(sat)}$	$I_c = 50 \text{ mA}, I_B = 5 \text{ mA}$			1.2	
DC current gain *	h_{FE}	$V_{CE} = 10 \text{ V}, I_c = 20 \text{ mA}$	50		400	
Insertion power gain	$ S_{21e} ^2$	$V_{CE} = 10 \text{ V}, I_c = 20 \text{ mA}, f = 1 \text{ GHz}$		11.5		dB
Noise figure	NF	$V_{CE} = 10 \text{ V}, I_c = 7 \text{ mA}, f = 1 \text{ GHz}$		1.1	2	
Reverse transfer capacitance	C_{re}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		0.55	1	pF
Transition frequency	f_t	$V_{CE} = 10 \text{ V}, I_c = 20 \text{ mA}$		7		GHz

*. Pulse measurement: $PW \leq 350 \mu\text{s}$, Duty Cycle $\leq 2\%$.

Typical Characteristics


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